Review of: "Although the distance is still on the scale of a few micrometers and the time is still measured in nanoseconds,"

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The high speed of switching (doping) in the nMOS transistor circuit of Graphene transistor is possible only because it can do p- and n (positive and negative) doping, and graphene doping is a main parameter in the development of nMOS transistor Graphene transistor. The bias voltage is applied to the graphene transistors in such a way that it always operates in its "active" region, that is, the curved or active linear part is used for the output characteristics. Graphene, which consists of only one carbon atom, can be used to create multilayer graphene field-effect transistors that consume less energy and take up less space. Graphene is a semi-conducting material with zero gap and not suitable for logic circuits, but using technology, they create different forms of this material that have different gaps. Graphene strips, multilayer graphene and graphene grown on different transistor layers are such forms.

Although the distance is still on the scale of a few micrometers and the time is still measured in nanoseconds, it essentially opens up the possibility of using rotation in microelectronic components.

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